

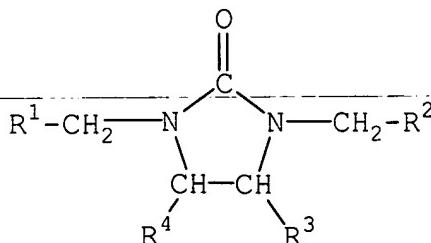
AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended) A negative-working photoresist composition which comprises, as a uniform solution in an organic solvent:

(A) 100 parts by weight of an alkali-soluble resin which is a copolymer of hydroxystyrene and styrene consisting of from 60 to 97% by moles of hydroxystyrene units and from 40 to 3% by moles of styrene units, a copolymer of hydroxystyrene and styrene consisting of from 60 to 97% by moles of hydroxystyrene units and from 40 to 3% by moles of styrene units substituted by alkali-insoluble groups for from 5 to 30% of the hydroxyl groups or a polyhydroxystyrene substituted by alkali-insoluble groups for from 3 to 40% of the hydroxyl groups;

(B) from 0.5 to 20 parts by weight of an onium salt compound selected from the group consisting of iodonium salt compounds and sulfonium salt compounds, of which the anionic moiety is a fluoroalkyl sulfonate anion as a radiation-sensitive acid-generating agent; and

(C) from 3 to 50 parts by weight of an ethyleneurea compound represented by the general formula



in which R¹ and R² are each a hydroxyl group or an alkoxy group having 1 to 4 carbon atoms and R³ and R⁴ are each a hydrogen atom, a hydroxyl group or an alkoxy group having 1 to 4 carbon atoms, as a crosslinking agent.

Claim 2 (Original) The negative-working photoresist composition as claimed in claim 1 in which the fluoroalkyl sulfonate anion in the component (B) is a perfluoroalkyl sulfonate anion having 1 to 10 carbon atoms.

Claim 3 (Cancelled)

Claim 4 (Currently Amended) The negative-working photoresist composition as claimed in claim [[3]] 1 in which the alkali-insoluble group is an alkyl group having 1 to 4 carbon atoms.

Claim 5 (Original) The negative-working photoresist composition as claimed in claim 1 in which at least one of the groups denoted by R¹ and R² is an alkoxy group having 1 to 4 carbon atoms, the rest, if any, being a hydroxyl group, and the groups denoted by R³ and R⁴ are each a hydrogen atom.

Claim 6 (Cancelled)

Claim 7 (Cancelled)

Claim 8 (Original) The negative-working photoresist composition as claimed in claim 1 which further comprises: (E) from 0.01 to 1.0 part by weight of a carboxylic acid per 100 parts by weight of the component (A).

Claim 9 (Original) The negative-working photoresist composition as claimed in claim 8 in which the component (E) is selected from the group consisting of malonic acid, citric acid, malic acid, succinic acid, benzoic acid and salicylic acid.

Claim 10 (Original) The negative-working photoresist composition as claimed in claim 1 in which the organic solvent is a mixture of propyleneglycol monomethyl ether and propyleneglycol monomethyl ether acetate in a mixing ratio in the range from 50:50 to 80:20 by weight.

Claim 11 (Original) A photosensitive material for patterning of a photoresist layer which comprises, as an integral layered body:

- (a) a substrate;
- (b) a water-insoluble organic anti-reflection coating film formed on the surface of the substrate; and
- (c) a photoresist layer formed on the anti-reflection coating film from a photoresist composition as defined in claim 1.

Claim 12 (Original) The photosensitive material for patterning of a photoresist layer as claimed in claim 11 in which the anti-reflection coating film has a thickness in the range from 30 to 300 nm.

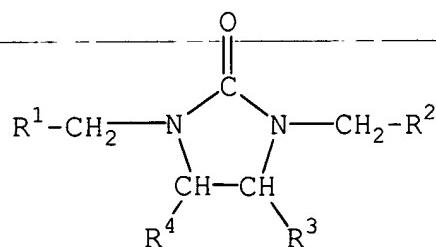
Claim 13 (Original) The photosensitive material for patterning of a photoresist layer as claimed in claim 11 in which the photoresist layer has a thickness in the range from 200 to 500 nm.

Claim 14 (Original) The photosensitive material for patterning of a photoresist layer as claimed in claim 11 which further comprises: (d) a water-soluble anti-reflection coating film formed on the photoresist layer.

Claim 15 (Original) The photosensitive material for patterning of a photoresist layer as claimed in claim 14 in which the water-soluble anti-reflection coating film has a thickness in the range from 35 to 45 nm.

Claim 16 (New) A negative-working photoresist composition which comprises, as a uniform solution in an organic solvent:

- (A) 100 parts by weight of an alkali-soluble resin;
- (B) from 0.5 to 20 parts by weight of an onium salt compound selected from the group consisting of iodonium salt compounds and sulfonium salt compounds, of which the anionic moiety is a fluoroalkyl sulfonate anion as a radiation-sensitive acid-generating agent;
- (C) from 3 to 50 parts by weight of an ethyleneurea compound represented by the general formula



in which R¹ and R² are each a hydroxyl group or an alkoxy group having 1 to 4 carbon atoms and R³ and R⁴ are each a hydrogen atom, a hydroxyl group or an alkoxy group having 1 to 4 carbon atoms, as a crosslinking agent and

- (D) from 0.01 to 1.0 part by weight of an aliphatic amine compound per 100 parts by weight of the component (A).

Claim 17 (New) The negative-working photoresist composition as claimed in claim 16 in which the fluoroalkyl sulfonate anion in the component (B) is a perfluoroalkyl sulfonate anion having 1 to 10 carbon atoms.

Claim 18 (New) The negative-working photoresist composition as claimed in claim 16 in which the alkali-insoluble group is an alkyl group having 1 to 4 carbon atoms.

Claim 19 (New) The negative-working photoresist composition as claimed in claim 16 in which at least one of the groups denoted by R¹ and R² is an alkoxy group having 1 to 4 carbon atoms, the rest, if any, being a hydroxyl group, and the groups denoted by R³ and R⁴ are each a hydrogen atom.

Claim 20 (New) The negative-working photoresist composition as claimed in claim 16 in which the aliphatic amine compound is selected from the group consisting of trialkyl amine compounds, dialkyl amine compounds, trialkanol amine compounds and dialkanol amine compounds, of which the alkyl group or alkanol group has 1 to 5 carbon atoms.

Claim 21 (New) The negative-working photoresist composition as claimed in claim 16 which further comprises: (E) from 0.01 to 1.0 part by weight of a carboxylic acid per 100 parts by weight of the component (A).

Claim 22 (New) The negative-working photoresist composition as claimed in claim 21 in which the component (E) is selected from the group consisting of malonic acid, citric acid, malic acid, succinic acid, benzoic acid and salicylic acid.

Claim 23 (New) The negative-working photoresist composition as claimed in claim 16 in which the organic solvent is a mixture of propyleneglycol monomethyl ether and propyleneglycol monomethyl ether acetate in a mixing ratio in the range from 50:50 to 80:20 by weight.

Claim 24 (New) A photosensitive material for patterning of a photoresist layer which comprises, as an integral layered body:

- (a) a substrate;
- (b) a water-insoluble organic anti-reflection coating film formed on the surface of the substrate; and
- (c) a photoresist layer formed on the anti-reflection coating film from a photoresist composition as defined in claim 16.

Claim 25 (New) The photosensitive material for patterning of a photoresist layer as claimed in claim 24 in which the anti-reflection coating film has a thickness in the range from 30 to 300 nm.

Claim 26 (New) The photosensitive material for patterning of a photoresist layer as claimed in claim 24 in which the photoresist layer has a thickness in the range from 200 to 500 nm.

Claim 27 (New) The photosensitive material for patterning of a photoresist layer as claimed in claim 24 which further comprises: (d) a water-soluble anti-reflection coating film formed on the photoresist layer.

Claim 28 (New) The photosensitive material for patterning of a photoresist layer as claimed in claim 27 in which the water-soluble anti-reflection coating film has a thickness in the range from 35 to 45 nm